

ABSTRACT OF THE DISCLOSURE

A semiconductor device has a plurality of gate bus wirings and source bus wirings on one of paired substrates. Moreover, an inter-layer insulating film made of an organic material is provided on thin film transistors of respective picture elements, and a picture element electrode is provided on the inter-layer insulating film. Furthermore, the semiconductor device is provided with an additional capacity common wiring which is provided on the inter-layer insulating film and forms an additional capacity section between the picture element electrode and the additional capacity common wiring.

20052345-012302